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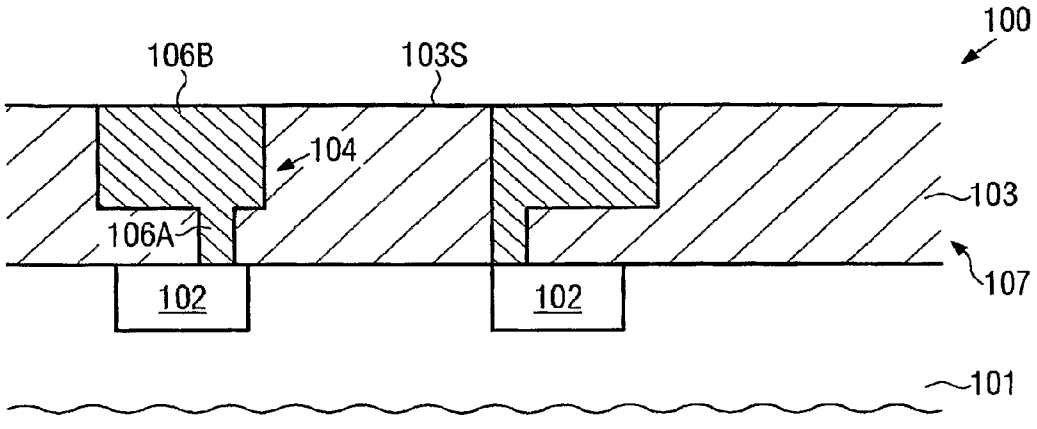
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(57) Abstract: By forming patterns for dual damascene metallization structures on the basis of an imprint technique, in which via openings and trenches are commonly formed in a moldable materia (103) by an imprint mold (150), a significant reduction of process complexity may be achieved due to the omission of at least one further alignment process as required in conventional process techniques. Furthermore, the flexibility and efficiency of imprint lithography may be increased by providing appropriately designed imprint molds in order to provide via openings and trenches exhibiting an increased fill capability, thereby also improving the performance of the finally obtained metallization structures with respect to reliability, resistance against electromigration and the like.

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